

	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	Inventor
1	US 6189582 B1	20011220	13	Small electrode for a chalcogenide switching device and method for fabricating same		257/3 ; 438/244 ; 438/95	Reinberg, Alan R. , et al.
2	US 6153890 A	20001128	19	Memory cell incorporating a chalcogenide element	257/3	257/2 ; 257/4 ; 257/5	Wolstenholme, Graham R. , et al.
3	US 6031287 A	20000229	24	Contact structure and memory element incorporating the same	257/734	257/758 ; 438/622	Harshfield, Steven T.
4	US 5751012 A	19980512	13	Polysilicon pillar diode for use in a non-volatile memory cell	257/5	257/2 ; 257/209 ; 257/37 ; 257/4 ; 257/530 ; 365/163	Wolstenholme, Graham R. , et al.
5	US 4177475 A	19791204	8	High temperature amorphous memory device for an electrically alterable read-only memory	257/2	257/616 ; 365/163	Holmberg, Scott H.
6	US 4115872 A	19780919	7	Amorphous semiconductor memory device for employment in an electrically alterable read-only memory	365/163	257/2	Bloom, Vernon A.

JP 04-645585 257/30,52